NPN Silicon Epitaxial Planar Transistor

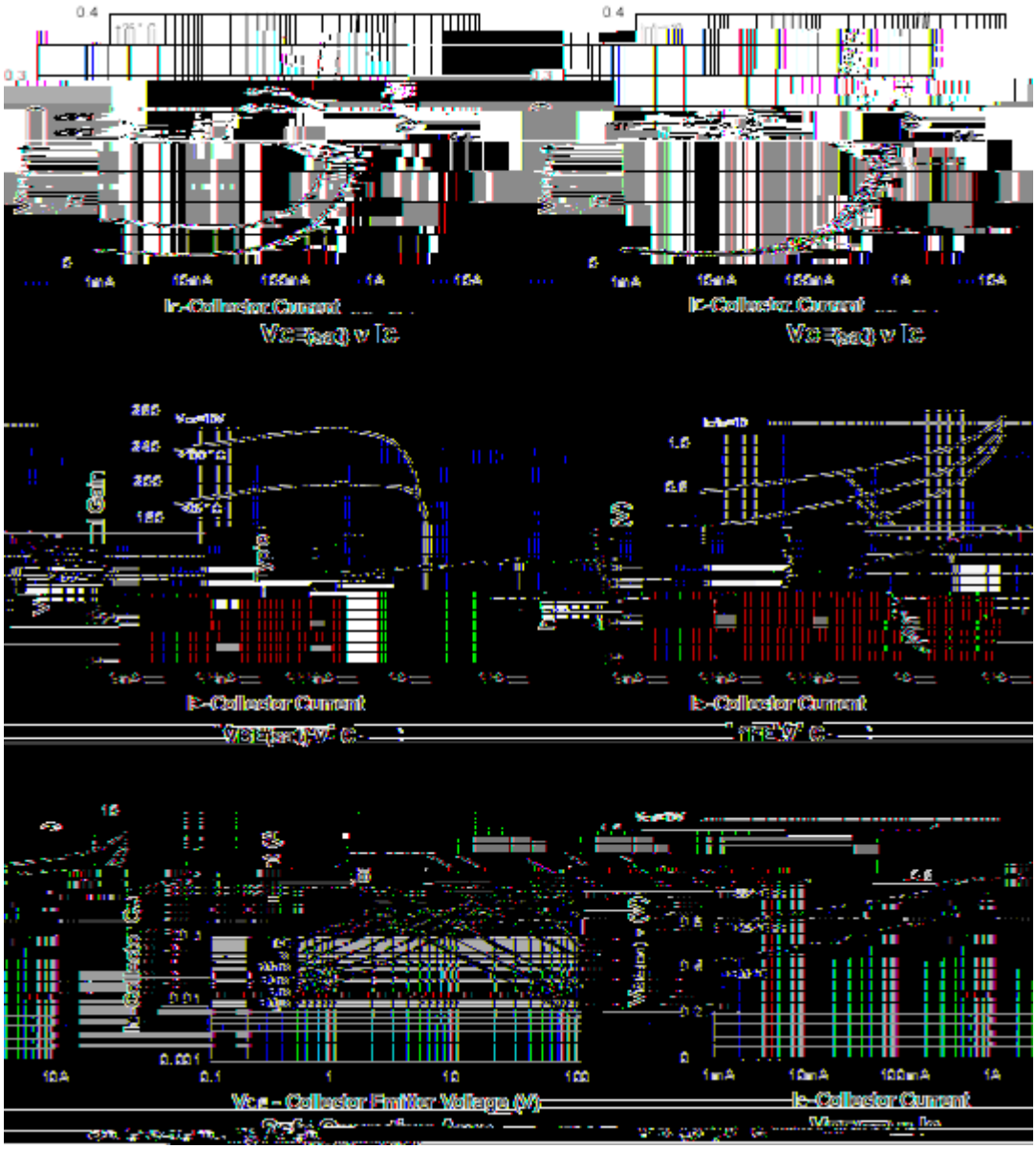
FEATURES

- Medium power transistor.
- Complementary To FMMT593.
- MSL 1

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
I_{CM}	Peak Pulse Current	2	A
P_C	Collector Dissipation	500	mW

℃

℃

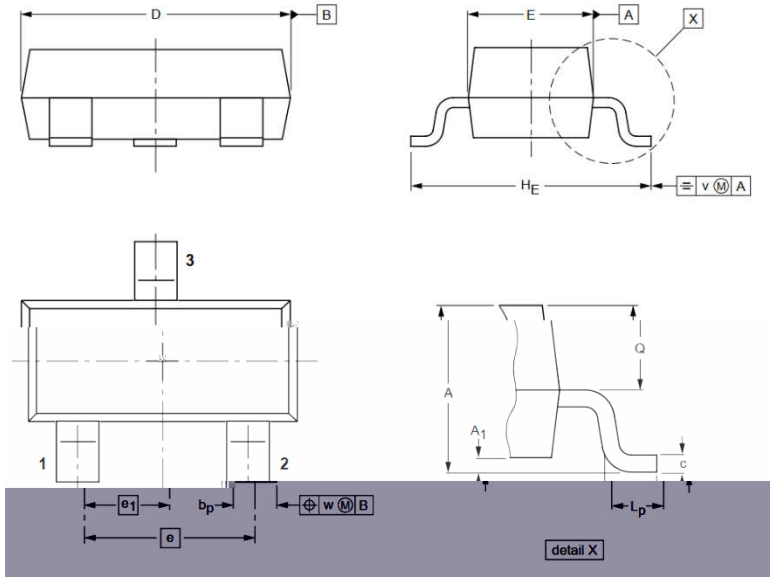

Ic-Collector Current
Ic-Collector Current
Ic-Collector Current
Ic-Collector Current
Vce - Collector Emitter Voltage (V)
Ic-Collector Current

Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
SOT-23			

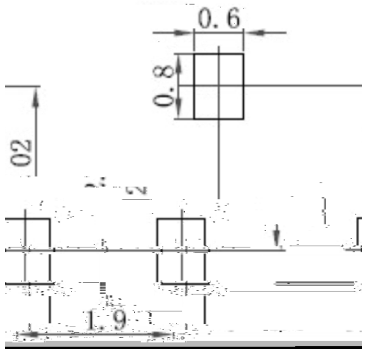
Package Dimensions

SOT-23



Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.

The recommended mounting pad size



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